



**Experiment title: High Pressure Diffraction Study of the New Superconducting Compound (Sr<sub>1-x</sub>K<sub>x</sub>)BiO<sub>3</sub>**

**Experiment number:**  
HS 617

**Beamline:**  
ID9

**Date of experiment:**  
from: 02/09/98 to: 06/09/98

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**Shifts:**  
12

**Local contact(s):**  
M. Hanfland

*Received at ESRF:*

**Names and affiliations of applicants (\* indicates experimentalists):**

**C. Chaillout-Bougerol, P. Bordet, S. Kazakov,  
Laboratoire de Cristallographie CNRS Grenoble**

### **Report:**

From resistivity measurements under pressure on Sr<sub>0.4</sub>K<sub>0.6</sub>BiO<sub>3</sub>, we found out that the superconducting transition temperature  $T_c$  was increasing slightly with pressure [3]. In order to check whether this increase of  $T_c$  was related to a change in symmetry, we have carried out a diffraction experiment under pressure on the ID9 beam line at ESRF (HS 617). Diffraction data have been collected up to 20GPa. The refinements have been done up to 10GPa only. We have observed a regular increase of the  $c/a$  ratio with pressure, indicating that the tetragonal distortion increases. The 6 Bi-O distances decrease and, as the two Bi-O1 ones diminish more rapidly than the four Bi-O2 ones, the distortion of the octahedra increases. Therefore, the increase of  $T_c$  is not related to an increase of the symmetry even on a local scale.

We have noticed a variation of the tilt angle of the BiO<sub>6</sub> octahedra around the  $c$  axis until a saturation at roughly 33° (45° is the value corresponding to the absence of tilt in the cubic symmetry) for a pressure of about 7GPa which is close to the pressure value at which the  $T_c$  is maximum.

At room pressure, we have calculated the formal valence on the Bi and (Sr,K) sites using the Bond Valence Sum method and the constants  $B$  and  $r_0$  reported by Brese et al.. We found  $v(\text{Bi}) = +5.2$  v.u., which is larger than the value +4.6 deduced from the chemical composition. This indicates that, at room pressure, the Bi site is compressed. For increasing pressure, it is not trivial to calculate the valences since we don't know how  $B$  and  $r_0$  change. However, it is possible to follow the evolution with pressure of the ratio of the average distances  $(C-O)_p / ((C-O)_{p=0})$  where  $C$  represents either Bi or (Sr,K). One observes that the external pressure affects more the (Sr,K) site than the Bi one. This can be taken, in other words, as an indication of a decrease of the charge on the Bi site; by analogy with the high  $T_c$  cuprates, pressure would therefore induce a change from an overdoped towards an optimally doped state.